Medium Power Transistor (25V, 1.2A) 2SD2537

Features

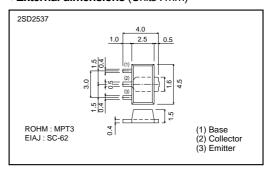
- 1) High DC current gain.
- 2) High emitter-base voltage. (VEBO=12V)
- 3) Low saturation voltage. (Max. VcE(sat)=0.3V at Ic/Iв=500mA/10mA)

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	Vсво	30	V	
Collector-emitter voltage	VCEO	25	V	
Emitter-base voltage	VEBO	12	V	
Collector current	lc.	1.2	A (DC)	
	IC IC	2	A (Pulse)*1	
Collector power dissipation	Pc	2	W *2	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55~+150	°C	

^{*1} Single pulse Pw=100ms *2 When mounted on a 40×40×0.7mm ceramic board.

●External dimensions (Units : mm)



●Packaging specifications and hfe

Type	2SD2537
	MPT3
Package	
hfe	VW
Marking	DV*
Code	T100
Basic ordering unit (pieces)	1000

^{*} Denotes hre

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	30	-	-	V	Ic=10μA	
Collector-emitter breakdown voltage	BVceo	25	-	-	V	Ic=1mA	
Emitter-base breakdown voltage	ВУево	12	-	-	V	Iε=10μA	
Collector cutoff current	Ісво	-	-	0.3	μΑ	VcB=30V	
Emitter cutoff current	Ієво	-	-	0.3	μΑ	V _{EB} =12V	
Collector-emitter saturation voltage	VcE(sat)	-	-	0.3	V	Ic/Iв=500mA/10mA	*
DC current transfer ratio	hre	820	-	2700	-	Vce/lc=5V/0.5A	
Transition frequency	f⊤	-	200	-	MHz	Vce=10V, Ie=-50mA, f=100MHz	*
Output capacitance	Cob	-	20	-	pF	Vcb=10V, Ie=0A, f=1MHz	

^{*}Measured using pulse current.

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